

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

Claims 1-6 (Cancelled)

Please add new claims 7-12 as follows:

7. (New) An exposure method for manufacturing a semiconductor integrated circuit device including a plurality of semiconductor devices formed on a substrate comprising the steps of:

forming a first pattern through exposure, said first pattern is partitioned by a plurality of device regions, in which each said device region a device group and a local interconnect are disposed, said device group including one or more semiconductor devices among said plurality of semiconductor devices and said local interconnect connecting said semiconductor devices included in said device group; and

after forming said first pattern, forming a second pattern through exposure, said second pattern is partitioned by a routing region in which a global routing is disposed, said global routing connecting said device group disposed in each said device region to each other,

wherein said global routing is disposed on said local interconnect,

wherein said local interconnect is provided only within each said device region and said global routing is provided only within said routing region,

wherein said routing region crosses each boundary between said plurality of device regions and is shifted from said plurality of device regions by a distance.

8. (New) The exposure method of claim 7,
wherein a dimension of each said device region and said routing region is set to be equal to or smaller than the size of one exposure region.

9. (New) The exposure method of claim 7,
wherein said plurality of device regions have one shape and are two-dimensionally arranged in a repetitive cycle corresponding to said shape, and
wherein said routing region is plural, and said plurality of routing regions have one shape, are two-dimensionally arranged in a repetitive cycle corresponding to said shape and are shifted from said plurality of device regions by a distance.

10. (New) The exposure method of claim 7,
wherein each said device region and said routing region has a same shape.

11. (New) The exposure method of claim 7,
wherein in the step of forming said first pattern, a routing terminal is formed in an interconnect layer for said local interconnect.

12. (New) The exposure method of claim 7,
wherein in the steps of forming said first pattern and said second pattern, exposure is performed using electromagnetic waves or a charged particle beam.